

TO-262K Plastic-Encapsulate Thyristors

CT316R 3Q TRIACs

MAIN CHARACTERISTICS

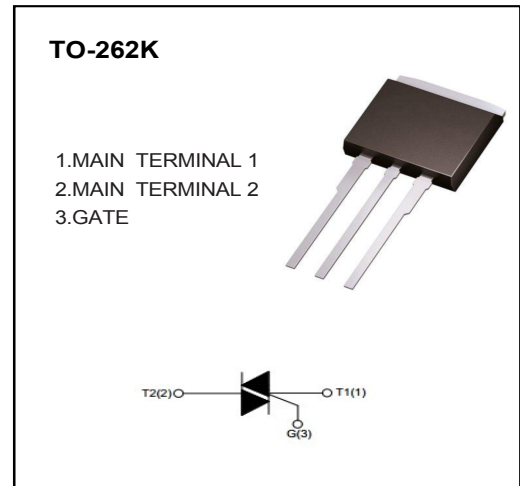
$I_{T(RMS)}$		16A
V_{DRM}/V_{RRM}	CT316R-600S/C/B	600V
	CT316R-800S/C/B	800V
V_{TM}		1.55V

FEATURES

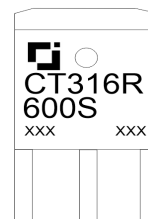
- NPNPN 5-layer Structure TRIACs
- Mesa Glass Passivated Technology
- Multi Layers Metal Electrodes
- High Junction Temperature
- Good Commutation Performance
- High dV/dt and dI/dt

APPLICATIONS

- Heater Control
- Motor Speed Controller
- Mixer



MARKING



CT316R:Series Code
600S:Depends on V_{DRM}
and I_{GT}
XXX:Internal Code

ABSOLUTE RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test condition	Value	Unit	
V_{DRM}/V_{RRM}	Repetitive peak off-state voltage	$T_j=25^\circ\text{C}$	CT316R-600S/C/B	600	V
			CT316R-800S/C/B	800	V
$I_{T(RMS)}$	RMS on-state current	TO-262K($T_c \leq 100^\circ\text{C}$), Fig. 1,2	16	A	
I_{TSM}	Non repetitive surge peak on-state current	Full sine wave , $T_j(\text{init})=25^\circ\text{C}$, $t_p=20\text{ms}$; Fig. 3,5	160	A	
I^2t	I^2t value	$t_p=10\text{ms}$	140	A^2s	
dI_T/dt	Critical rate of rise of on-state current	$I_G=2 \cdot I_{GT}$, $t_r \leq 10\text{ns}$, $F=120\text{Hz}$, $T_j=125^\circ\text{C}$	I - II - III	50	$\text{A}/\mu\text{s}$
			IV	n/a	
I_{GM}	Peak gate current	$t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$	4	A	
$P_{G(AV)}$	Average gate power	$T_j=125^\circ\text{C}$	1	W	
T_{STG}	Storage temperature		-40~+150	$^\circ\text{C}$	
T_j	Operating junction temperature		-40~+125		

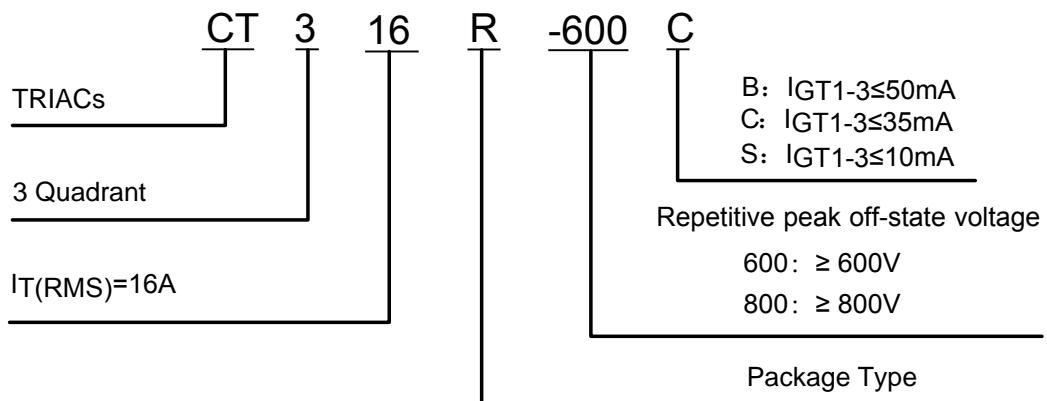
ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Symbol	Parameter	Test condition	Value			Unit	
			S	C	B		
I _{GT}	Gate trigger current	V _D =12V, R _L =33Ω, T _j =25°C, Fig. 6	I - II -III	≤10	≤35	≤50	mA
			IV	n/a	n/a	n/a	
V _{GT}	Gate trigger voltage	T _j =25°C, Fig. 6	I - II -III	≤1.3		V	
V _{GD}	Non-triggering gate voltage	V _D =V _{DRM} , T _j =125°C		≥0.2		V	
I _H	Holding current	I _T =500mA, Fig. 6		≤15	≤30	≤50	mA
I _L	Latching current	I _G =1.2I _{GT} Fig. 6	I - III	≤25	≤50	≤70	mA
			II	≤30	≤60	≤80	mA
dV _D /dt	Critical rate of rise of off-state	V _D =67%V _{DRM} , Gate Open T _j =125°C		≥40	≥500	≥1000	V/μs
V _{TM}	On-state Voltage	I _{TM} =23A, tp=380μs, Fig. 4		≤1.55		V	
I _{DRM} / I _{RPM}	Repetitive peak off-state current	V _D =V _{DRM} /V _{RPM} , T _j =25°C		≤5	≤5	≤5	μA
		V _D =V _{DRM} /V _{RPM} , T _j =125°C		≤1	≤1	≤1	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th} (j-c)	Junction to case (AC)	TO-262K	1.2 °C/W
R _{th} (j-a)	Junction to ambient	TO-262K	45 °C/W

PART NUMBER



CHARACTERISTICS CURVES

FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

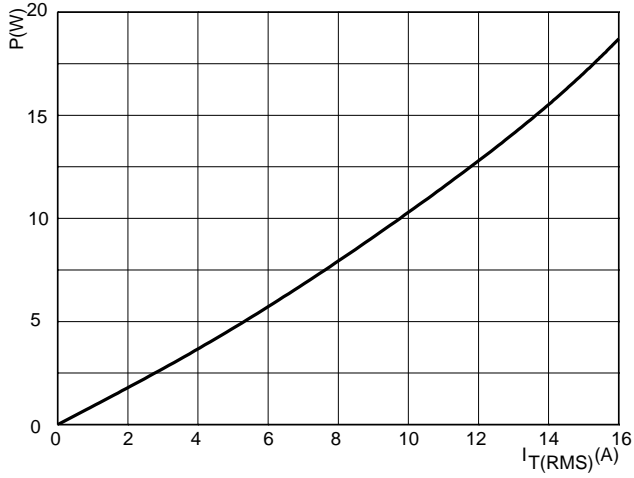


FIG.2: RMS on-state current versus case temperature (full cycle)

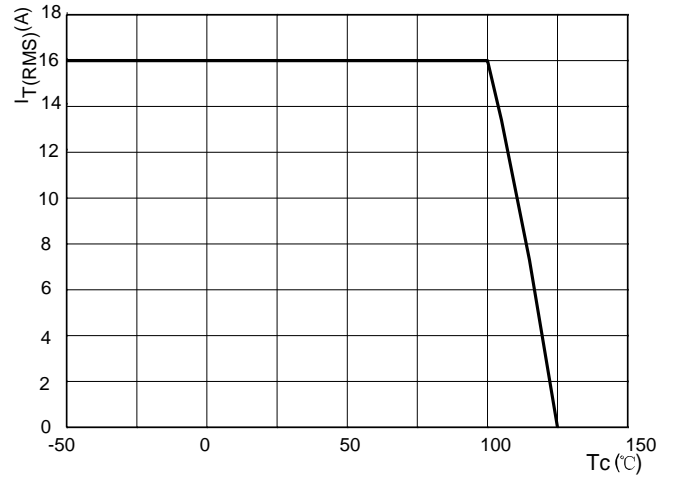


FIG.3: Surge peak on-state current versus number of cycles

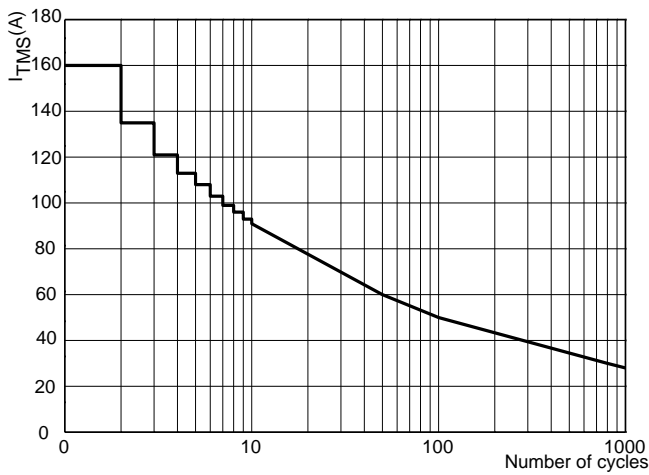


FIG.4: On-state characteristics (maximum values)

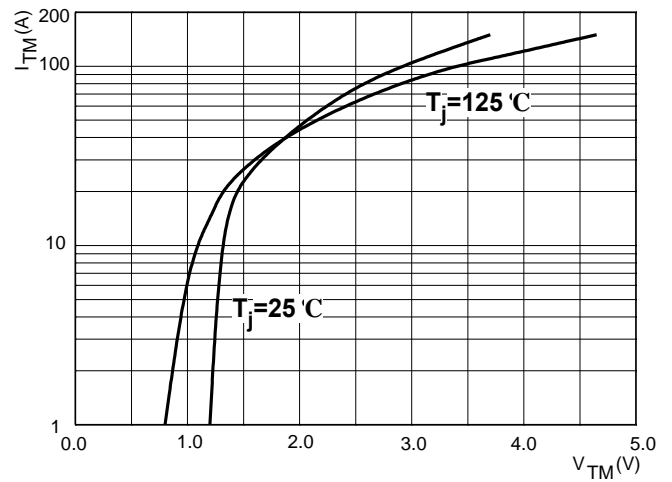


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$

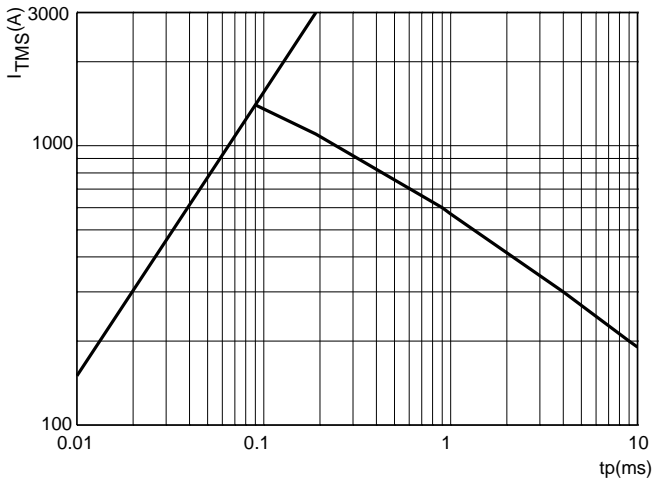
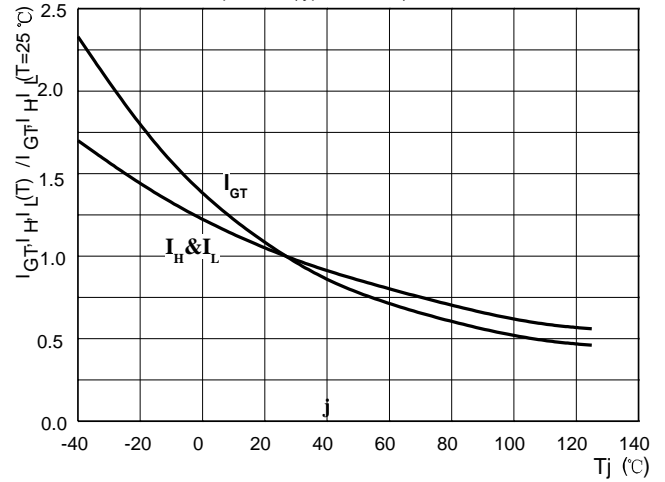
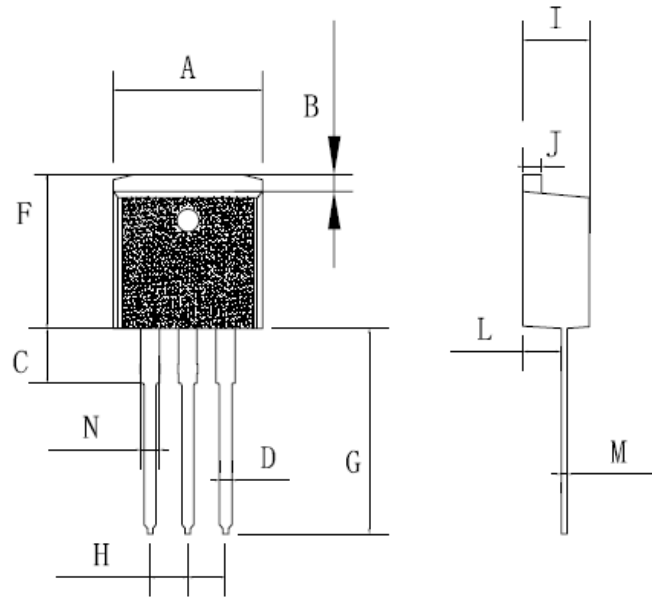


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)



TO-262K PACKAGE OUTLINE DIMENSIONS



DIM.	Unit(mm)		Unit(inch)	
	Min	Max	Min	Max
A	9.7	10.4	0.381	0.409
B	1.31	1.62	0.051	0.063
C	3.5	3.9	0.137	0.153
D	0.7	0.92	0.027	0.036
F	9.95	10.35	0.391	0.407
G	12.95	13.9	0.509	0.547
H	2.4	2.7	0.094	0.106
I	4.38	4.65	0.172	0.183
J	1.15	1.36	0.045	0.053
L	2.35	2.85	0.092	0.112
M	0.32	0.58	0.012	0.022
N	1.18	1.42	0.046	0.055